

PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors;
R1 = 2.2 k Ω , R2 = open

Rev. 01 — 31 March 2006

Product data sheet

1. Product profile

1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP complement	NPN/PNP complement
	Philips	JEITA		
PEMD30	SOT666	-	PEMB30	PEMH30
PUMD30	SOT363	SC-88	PUMB30	PUMH30

1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Cost-saving alternative for BC847BPN and BC847BVN
- Switching loads

1.4 Quick reference data

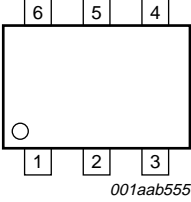
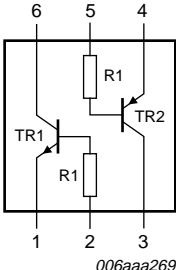
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω

PHILIPS

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1	 001aab555	 006aaa269
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMD30	-	plastic surface-mounted package; 6 leads	SOT666
PUMD30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMD30	2U
PUMD30	*B3

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	-	50	V	
V _{CEO}	collector-emitter voltage	open base	-	50	V	
V _{EBO}	emitter-base voltage	open collector	-	5	V	
I _O	output current		-	100	mA	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW
T _{stg}	storage temperature		-65	+150	°C	
T _j	junction temperature		-	150	°C	
T _{amb}	ambient temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		[1]	-	-	625	K/W
	SOT666		[1][2]	-	-	625	K/W
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		[1]	-	-	416	K/W
	SOT666		[1][2]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

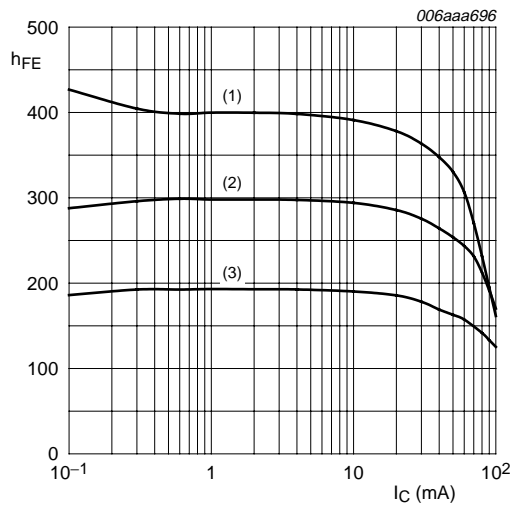
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

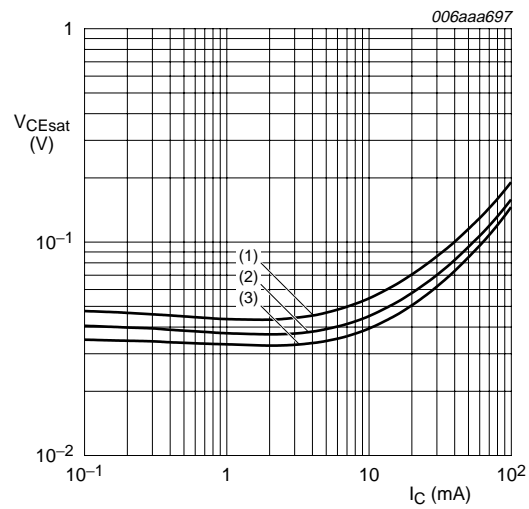
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	μA
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150^{\circ}\text{C}$	-	-	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 20\text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$				
		TR1 (NPN)	-	-	2.5	pF
		TR2 (PNP)	-	-	3	pF



$V_{CE} = 5 \text{ V}$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

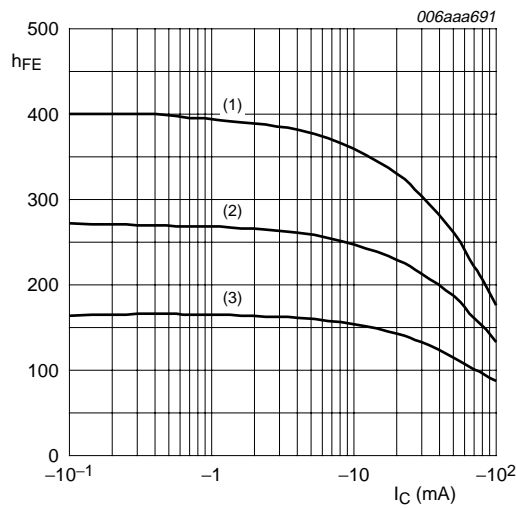
Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

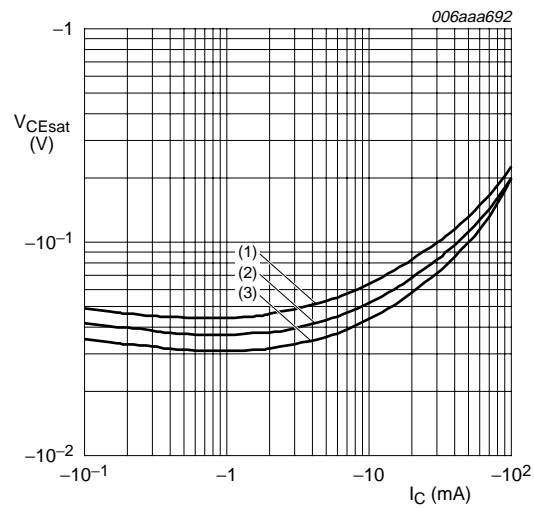
Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = -5 \text{ V}$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 3. TR2 (PNP): DC current gain as a function of collector current; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3) $T_{amb} = -40 \text{ }^\circ\text{C}$

Fig 4. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline

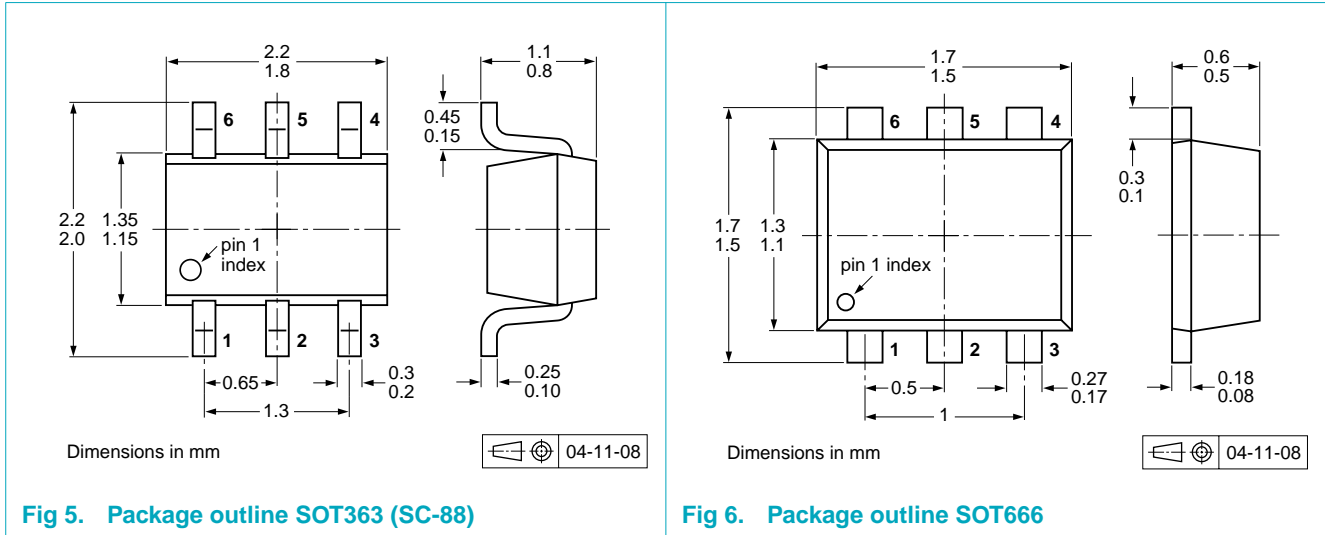


Fig 5. Package outline SOT363 (SC-88)

Fig 6. Package outline SOT666

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

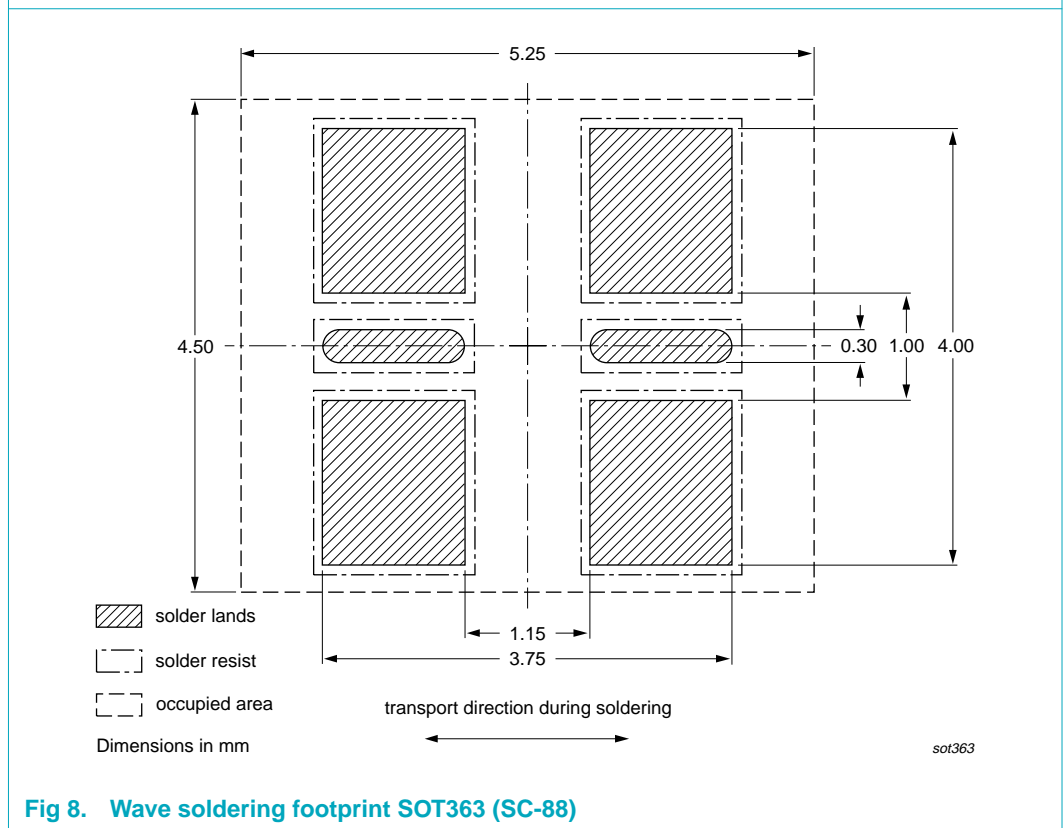
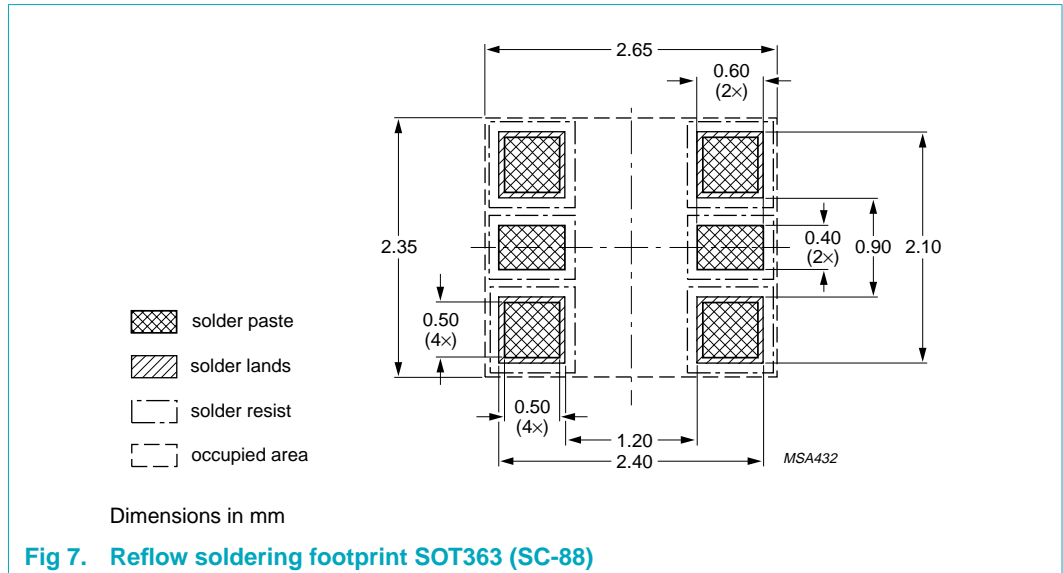
Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMD30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMD30	SOT363	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-	-	-165

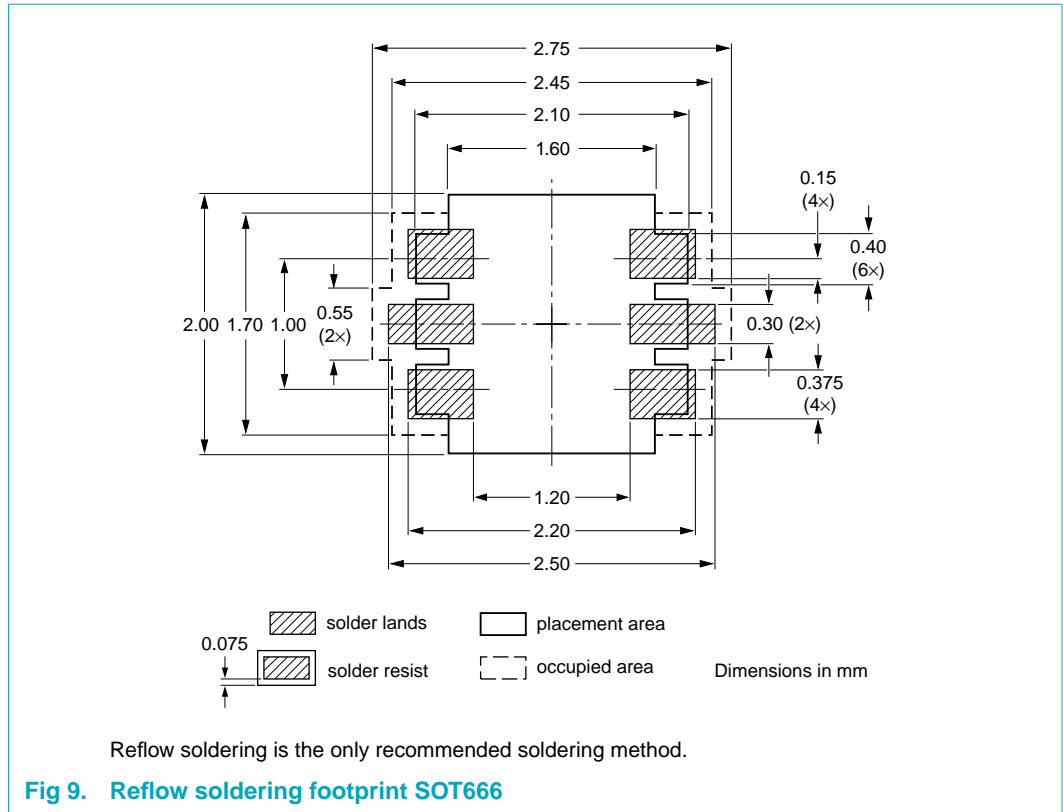
[1] For further information and the availability of packing methods, see [Section 13](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Soldering





11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD30_PUMD30_1	20060331	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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